



Bipolar PNP Bare Die – BTP069

Part Description

The BTP069 is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Driver applications. NPN complement is BTN069

Key Parameters:

- VCBO = -400V
- VCEO = -400V
- VEBO = -6V
- hFE = 80-300 @ VCE = -10V, IC = -0.01A
- VCE(Sat) = -0.75V @ IC = -0.05A, IB = -5mA
- fT = 50 MHz @ VCE = -10V, IE = 0A
- COBO = 4pF @ VCB = -20V

Features

Designed to provide performance equivalent to MPSA94

Die Size (Unawn)

850 μ m X 850 μ m, 33 Mils X 33 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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